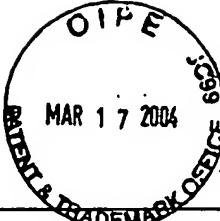


10/731,341

FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT



Applicant(s): Brian A.Floyd
Docket No.: YOR920030585US1
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Filing Date: December 9, 2003
Group: 2817

U.S. PATENT DOCUMENTS

EXAMINER	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE
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FOREIGN PATENT DOCUMENTS

EXAMINER	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION
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OTHER DOCUMENTS

EXAMINER	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
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- 1. L. Tran et al., "High Performance, High Yield Millimeter-Wave MMIC LNAs Using InP HEMTs," IEEE IMS Digest, p. 9-12, June 1996.
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- 4. K. Nishikawa et al. "Compact LNA and VCO 3-D MMICs Using Commercial GaAs PHEMT Technology for V-band Single-chip TRX MMIC," IEEE IMS Digest, p. 1717-1720, June 2002.
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NGUYEN, KV

4/21/05

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.